

N-Channel Enhancement Mode MOSFET

1. Product Information

1.1 Features

- ☒ Surface-mounted package
- ☒ Advanced trench cell design
- ☒ 100% Avalanche Tested
- ☒ 100% DVDS Tested
- ☒ $T_{J\max}$ 175°C

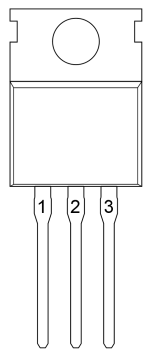
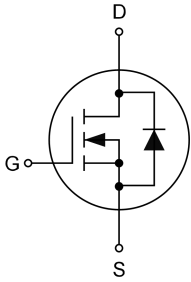
1.2 Applications

- ☒ DC/DC Conversion
- ☒ Power Switch
- ☒ Motor Drives
- ☒ Battery management

1.3 Quick reference

- ☒ $BV \geq 100\text{ V}$
- ☒ $R_{DS(ON)} \leq 2.0\text{ m}\Omega @ V_{GS} = 10\text{ V}$
- ☒ $P_D \leq 326\text{ W}$
- ☒ $I_D \leq 289\text{ A}$

2. Pin Description

Pin	Description	Simplified Outline	Symbol
1	Gate		
2	Source		
3	Drain		

Top View
TO-220

3. Limiting Values

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	Drain-Source Voltage	$T_C=25^{\circ}\text{C}$	100	-	V
V_{GS}	Gate-Source Voltage	$T_C=25^{\circ}\text{C}$	-	± 20	V
I_D	Drain Current (DC)	$T_C=25^{\circ}\text{C}, V_{GS}=10\text{ V}$	-	289	A
		$T_C=100^{\circ}\text{C}, V_{GS}=10\text{ V}$	-	204	A
I_{DM}^*	Drain Current (Pulsed)	$T_C=25^{\circ}\text{C}, V_{GS}=10\text{ V}$	-	1156	A
P_D	Drain power dissipation	$T_C=25^{\circ}\text{C}$	-	326	W
E_{AS}	Single Pulsed Avalanche Energy	$V_{DD}=50\text{ V}, L=0.5\text{ mH}$	-	1250	mJ
T_J, T_{stg}	Operating Junction and Storage Temperature Range		-55	175	$^{\circ}\text{C}$
$R_{\theta JA}$	Thermal Resistance-Junction to Ambient		-	45	$^{\circ}\text{C}/\text{W}$
$R_{\theta JC}$	Thermal Resistance-Junction to Case		-	0.46	

Notes:

- * Pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
- ** Surface mounted on 1 in² pad area, $t \leq 10\text{ sec}$.
- *** Limited by bonding wire.

4. Marking Information

Product Name	Marking
KJ020N10CA	KJ020N10CA XXXXXX-X

5. Ordering Code

Product Name	Package	Packaging	Quantity (pcs)	Note
KJ020N10CA	TO-220	Tube	1000	

Note: KUAJIEXIN defines "Green" as lead-free (RoHS compliant) and halogen free (Br or Cl does not exceed 900 ppm by weight in homogeneous material and total of Br and Cl does not exceed 1500 ppm by weight; Follow IEC 61249-2-21 and IPC/JEDEC J-STD-020C).

6. Electrical Characteristics (T_A=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0 V, I _{DS} =250 μA	100	-	-	V
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _{DS} =250 μA	2	-	4	V
I _{DSS}	Drain Leakage Current	V _{DS} =80 V, V _{GS} =0 V	-	-	1	μA
I _{GSS}	Gate Leakage Current	V _{DS} =0 V, V _{GS} =±20 V	-	-	±100	nA
R _{DS(ON)}	On-State Resistance	V _{GS} =10 V, I _{DS} =50 A	-	1.8	2.0	mΩ
Diode Characteristics						
V _{SD}	Diode Forward Voltage	V _{GS} =0 V, I _{SD} =50 A	-	-	1.2	V
t _{rr}	Reverse Recovery Time	V _{GS} =0 V, I _{DS} =50 A, dI _{SD} /dt=100 A/μs	-	104	-	ns
Q _{rr}	Reverse Recovery Charge		-	285	-	nC
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{DS} =50 V, V _{GS} =0 V, Frequency=1 MHz	-	9720	-	pF
C _{oss}	Output Capacitance		-	1500	-	
C _{rss}	Reverse Transfer Capacitance		-	55	-	
t _{d(on)}	Turn-on Delay Time	V _{DS} =50 V, V _{GEN} =10 V, R _G =2 Ω, R _L =1 Ω, I _{DS} =50 A	-	36	-	ns
t _r	Turn-on Rise Time		-	30	-	
t _{d(off)}	Turn-off Delay Time		-	82	-	
t _f	Turn-off Fall Time		-	30	-	
Gate Charge Characteristics						
Q _g	Total Gate Charge	V _{DS} =50 V, V _{GS} =10 V, I _{DS} =50 A	-	195	-	nC
Q _{gs}	Gate-Source Charge		-	53	-	
Q _{gd}	Gate-Drain Charge		-	56	-	

7. Typical Characteristics

7. Typical Characteristics (cont.)

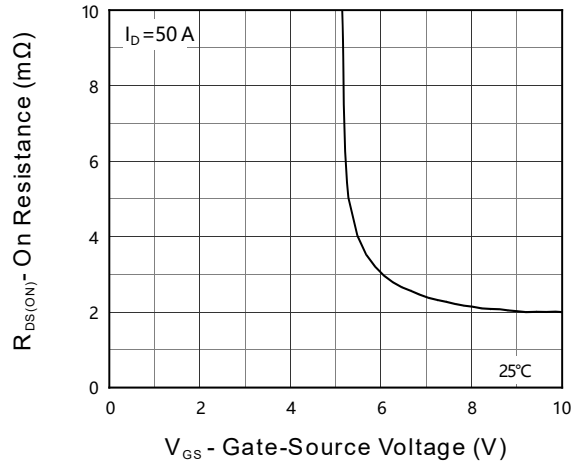


Figure 7. Transfer Characteristics

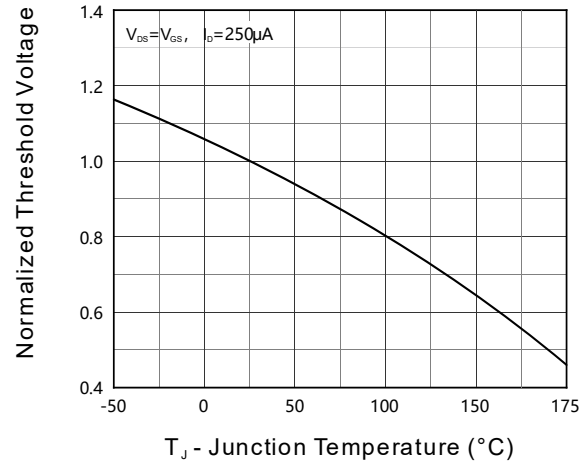


Figure 8. Normalized Threshold Voltage

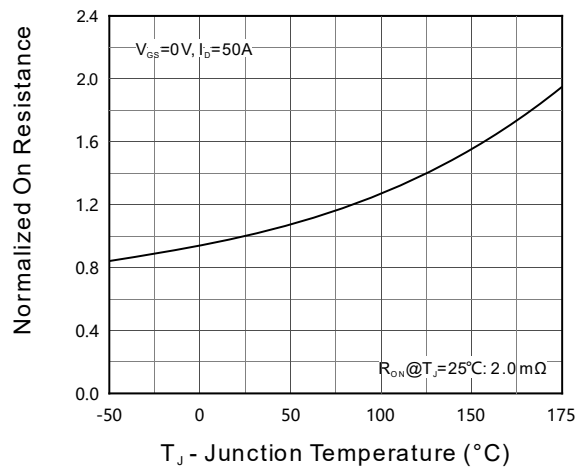


Figure 9. Normalized On Resistance

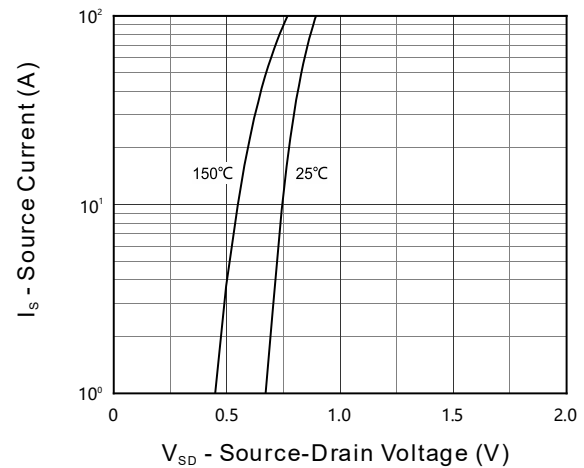


Figure 10. Diode Forward Current

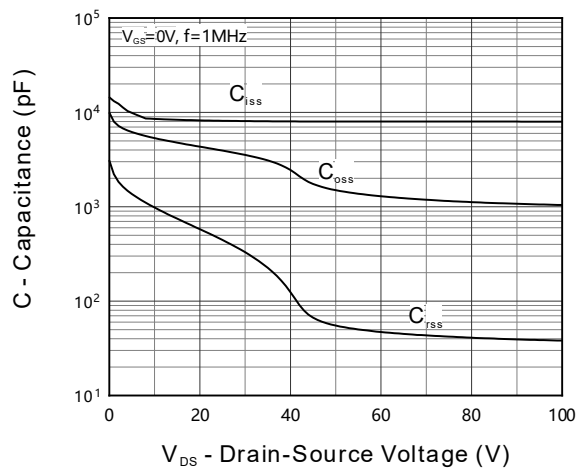


Figure 11. Capacitance

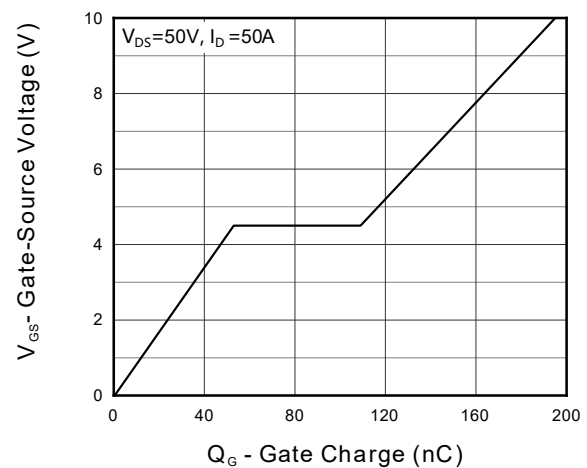
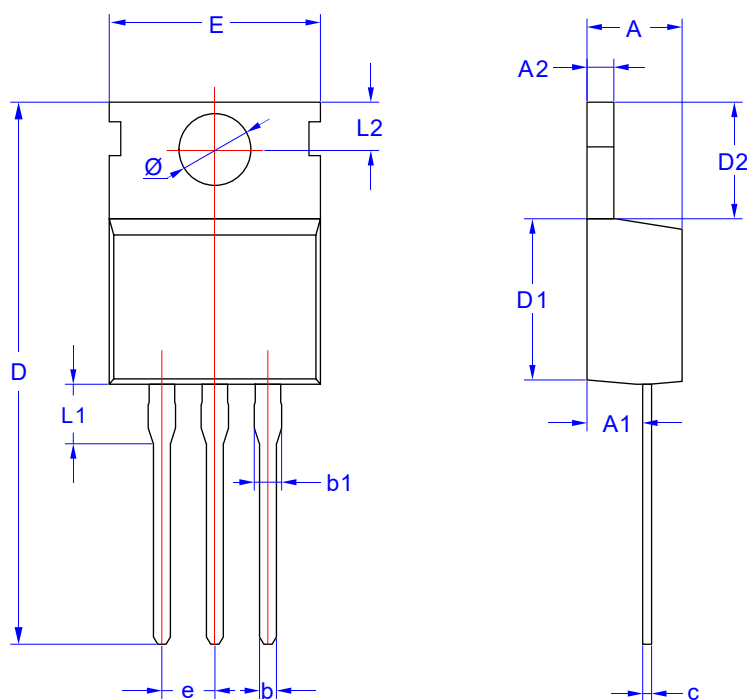


Figure 12. Gate Charge

8. Package Dimensions

TO-220 Package



Symbol	Dimensions in Millimeters	
	MIN	MAX
A	4.24	4.70
A1	2.20	3.00
A2	1.15	1.40
b	0.70	0.95
b1	1.14	1.70
c	0.40	0.60
D	28.0	29.8
D1	8.80	9.90
D2	6.25	6.90
E	9.70	10.50
L1	3.80	
L2	2.40	3.00
e	2.54 BSC	
Φ	3.60	